

**TABLE 1(a) - TYPE VARIANTS**

VARIANT	CASE	FIGURE	LEAD MATERIAL AND/OR FINISH
01	FLAT	2(a)	G2 or G8
02	FLAT	2(a)	G4
03	D.I.L.	2(b)	G2 or G8
04	D.I.L.	2(b)	G4
07	CHIP CARRIER	2(c)	2
08	D.I.L.	2(d)	G2
09	D.I.L.	2(d)	G4
10	SO CERAMIC	2(e)	G2
11	SO CERAMIC	2(e)	G4

TABLE 1(b) - MAXIMUM RATINGS

NO.	CHARACTERISTICS	SYMBOL	MAXIMUM RATINGS	UNITS	REMARKS
1	Supply Voltage	V_{DD}	-0.5 to +18	V	Note 1
2	Input Voltage	V_{IN}	-0.5 to $V_{DD} + 0.5$	V	Note 2 Power on
3	D.C. Input Current	$\pm I_{IN}$	10	mA	-
4	D.C. Output Current	$\pm I_{O}$	10	mA	Note 3
5	Device Dissipation	P_D	200	mWdc	Per Package
6	Output Dissipation	P_{DSO}	100	mWdc	Note 4
7	Operating Temperature Range	T_{op}	-55 to +125	°C	-
8	Storage Temperature Range	T_{stg}	-65 to +150	°C	-
9	Soldering Temperature For FP and DIP For CCP	T_{sol}	+300 +245	°C	Note 5 Note 6

NOTES

- Device is functional from +3V to +15V with reference to V_{SS} .
- $V_{DD} + 0.5V$ should not exceed +18V.
- The maximum output current of any single output.
- The maximum power dissipation of any single output.
- Duration 10 seconds maximum at a distance of not less than 1.5mm from the device body and the same lead shall not be resoldered until 3 minutes have elapsed.
- Duration 30 seconds maximum and the same terminal shall not be resoldered until 3 minutes have elapsed.



TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - d.c. PARAMETERS (CONT'D)

NO.	CHARACTERISTICS	SYMBOL	TEST METHOD MIL-STD 883	TEST FIG.	TEST CONDITIONS (PINS UNDER TEST D/F = DIP AND FP C = CCP)	LIMITS		UNIT
						MIN	MAX	
274	Input Voltage Low Level (Noise Immunity) (Functional Test)	V_{IL1}	-	4(h)	Address and Inhibit Inputs: $V_{IL} = 1.5V_{dc}$, $V_{IH} = 3.5V_{dc}$ Channel Input: $V_{IL} = 0V_{dc}$, $V_{IH} = 5V_{dc}$ $V_{DD} = 5V_{dc}$, $V_{SS} = V_{EE} = 0V_{dc}$ Note 5 (Pins D/F 1-2-4-5-11-12-14-15) (Pins C 1-2-5-6-14-15-17-19)	-	0.5	V
	Input Voltage High Level (Noise Immunity) (Functional Test)	V_{IH1}				4.5	-	
275	Input Voltage Low Level (Noise Immunity) (Functional Test)	V_{IL2}	-	4(h)	Address and Inhibit Inputs: $V_{IL} = 4V_{dc}$, $V_{IH} = 11V_{dc}$ Channel Input: $V_{IL} = 0V_{dc}$, $V_{IH} = 15V_{dc}$ $V_{DD} = 15V_{dc}$, $V_{SS} = V_{EE} = 0V_{dc}$ Note 5 (Pins D/F 1-2-4-5-11-12-14-15) (Pins C 1-2-5-6-14-15-17-19)	-	1.5	V
	Input Voltage High Level (Noise Immunity) (Functional Test)	V_{IH2}				13.5	-	
276	Threshold Voltage N-Channel	V_{THN}	-	4(i)	Inhibit and V_{EE} at Ground. All Other Inputs: $V_{IN} = 5V_{dc}$ $V_{DD} = 5V_{dc}$, $I_{SS} = -10\mu A$ (Pin D/F 8) (Pin C 10)	-0.7	-3.0	V
277	Threshold Voltage P-Channel	V_{THP}	-	4(j)	Inhibit at Ground. All Other Inputs: $V_{IN} = -5V_{dc}$ $V_{SS} = V_{EE} = -5V_{dc}$, $I_{DD} = 3.5\mu A$ (Pin D/F 16) (Pin C 20)	0.7	3.0	V
278 to 280	Input Clamp Voltage (to V_{SS})	V_{IC1}	-	4(k)	I_{IN} (Under Test) = $-100\mu A$ $V_{DD} = \text{Open}$, $V_{SS} = 0V_{dc}$ All Other Pins Open (Pins D/F 6-9-10) (Pins C 7-11-12)	-	-2.0	V
281 to 283	Input Clamp Voltage (to V_{DD})	V_{IC2}	-	4(l)	V_{IN} (Under Test) = $6V_{dc}$ $V_{SS} = \text{Open}$, $R = 30k\Omega$; (Pins D/F 6-9-10) (Pins C 7-11-12)	3.0	-	V

NOTES: See Page 25.

**TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - a.c. PARAMETERS**

NO.	CHARACTERISTICS	SYMBOL	TEST METHOD MIL-STD 883	TEST FIG.	TEST CONDITIONS (PINS UNDER TEST D/F = DIP AND FP C = CCP)	LIMITS		UNIT
						MIN	MAX	
284 to 286	Input Capacitance Address or Inhibit	C_{IN}	3012	4(m)	V_{IN} (Not Under Test) = 0Vdc $V_{DD} = V_{SS} = V_{EE} = 0Vdc$ Note 6 (Pins D/F 6-9-10) (Pins C 7-11-12)	-	7.5	pF
287 to 294	Channel Capacitance (Input)	C_{INC}	3012	4(n)	$V_{DD} = V_{SS} = V_{EE} = 0Vdc$ Note 6 (Pins D/F 1-2-4-5-11-12- 14-15) (Pins C 1-2-5-6-14-15-17- 19)	-	7.5	pF
295 to 296	Channel Capacitance (Output)	C_{OC}	3012	4(o)	$V_{DD} = V_{SS} = V_{EE} = 0Vdc$ Note 6 (Pins D/F 3-13) (Pins C 4-16)	-	30	pF
297	Propagation Delay Channel Input to Channel Output	t_{PLH1}	3003	4(q)	V_{IN} (Under Test) = Pulse Generator $V_{IL} = 0Vdc$, $V_{IH} = 5Vdc$ $R_L = 200k\Omega$ $V_{DD} = 5Vdc$, $V_{SS} = V_{EE} = 0Vdc$ Note 7 <u>Pins D/F</u> <u>Pins C</u> 13 to 12 16 to 15	-	40	ns
298	Propagation Delay Address to Signal OUT (Channel turning ON)	t_{PLH2}	3003	4(p)	V_{IN} (Under Test) = Pulse Generator $V_{IL} = 0Vdc$, $V_{IH} = 5Vdc$ $R_L = 10k\Omega$ $V_{DD} = 5Vdc$, $V_{SS} = V_{EE} = 0Vdc$ Note 7 <u>Pins D/F</u> <u>Pins C</u> 10 to 3 12 to 4	-	720	ns
299	Propagation Delay Inhibit to Signal OUT (Channel turning ON)	t_{PLH3}	3003	4(p)	V_{IN} (Under Test) = Pulse Generator $V_{IL} = 0Vdc$, $V_{IH} = 5Vdc$ $R_L = 10k\Omega$ $V_{DD} = 5Vdc$, $V_{SS} = V_{EE} = 0Vdc$ Note 7 <u>Pins D/F</u> <u>Pins C</u> 6 to 3 7 to 4	-	400	ns

NOTES: See Page 25.

**TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - a.c. PARAMETERS (CONT'D)**

NO.	CHARACTERISTICS	SYMBOL	TEST METHOD MIL-STD 883	TEST FIG.	TEST CONDITIONS (PINS UNDER TEST D/F = DIP AND FP C = CCP)	LIMITS		UNIT
						MIN	MAX	
300	Propagation Delay Channel Input to Channel Output	t_{PHL1}	3003	4(q)	V_{IN} (Under Test) = Pulse Generator $V_{IL} = 0V_{dc}$, $V_{IH} = 5V_{dc}$ $R_L = 200k\Omega$ $V_{DD} = 5V_{dc}$, $V_{SS} = V_{EE} = 0V_{dc}$ Note 7 <u>Pins D/F</u> <u>Pins C</u> 13 to 12 16 to 15	-	40	ns
301	Propagation Delay Address to Signal OUT (Channel turning OFF)	t_{PHL2}	3003	4(p)	V_{IN} (Under Test) = Pulse Generator $V_{IL} = 0V_{dc}$, $V_{IH} = 5V_{dc}$, $R_L = 300\Omega$ $V_{DD} = 5V_{dc}$, $V_{SS} = V_{EE} = 0V_{dc}$ Note 7 <u>Pins D/F</u> <u>Pins C</u> 10 to 3 12 to 4	-	720	ns
302	Propagation Delay Inhibit to Signal OUT (Channel turning OFF)	t_{PHL3}	3003	4(p)	V_{IN} (Under Test) = Pulse Generator $V_{IL} = 0V_{dc}$, $V_{IH} = 5V_{dc}$ $R_L = 300\Omega$ $V_{DD} = 5V_{dc}$, $V_{SS} = V_{EE} = 0V_{dc}$ Note 7 <u>Pins D/F</u> <u>Pins C</u> 6 to 3 7 to 4	-	400	ns

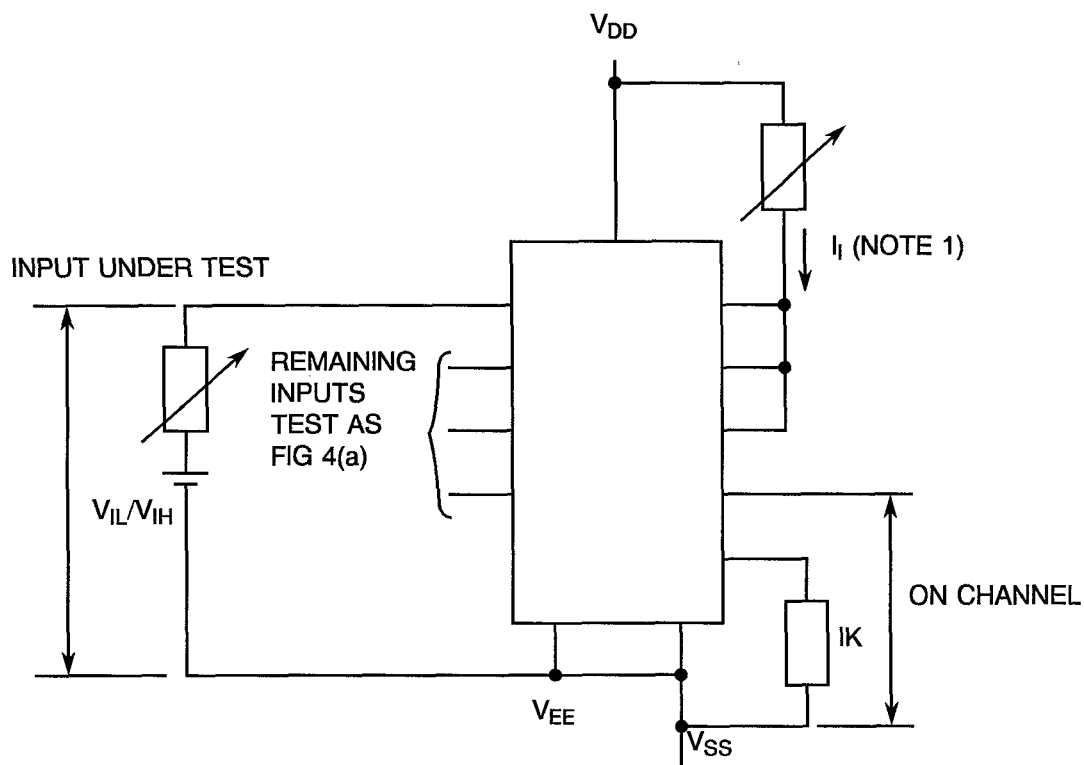
NOTES

- GO-NO-GO Test, each pattern of Test Table 4(a).
 $V_{OH} \geq V_{DD} - 0.5V_{dc}$ $V_{OL} \leq 0.5V_{dc}$
- Maximum time to output comparator strobe 300 μ sec.
- Measure each value of I_{DD} for the input conditions given in Table 4(b).
- For characterisation during qualification, the incremental method or the method shown in Figure 4(g)(ii), which incorporates a plotter, shall apply. For procurement, the Orderer may accept that the devices are tested go-no-go to the maximum limits of Table 2. In the case that go-no-go testing is performed, it is necessary that at least one discrete value shall be measured and recorded in order that drift values may be applied. Figure 4(g)(iii) shall be used for the discrete value measurement.
- This is performed as a Functional Test in which extreme V_{IN} conditions are applied and channel selection is monitored.
- Measurement performed on a sample basis, LTPD 7 or less, with a Capacitance Bridge connected between each input or output under test and V_{SS} , only for Lots where LAT Level 2 is to be performed. (For LTPD sampling plan, see Annexe I of ESA/SCC 9000).
- Measurement performed on a sample basis LTPD 7, or less (see Annexe I of ESA/SCC 9000).



FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS (CONTINUED)

FIGURE 4(h) - INPUT VOLTAGE HIGH AND LOW LEVEL



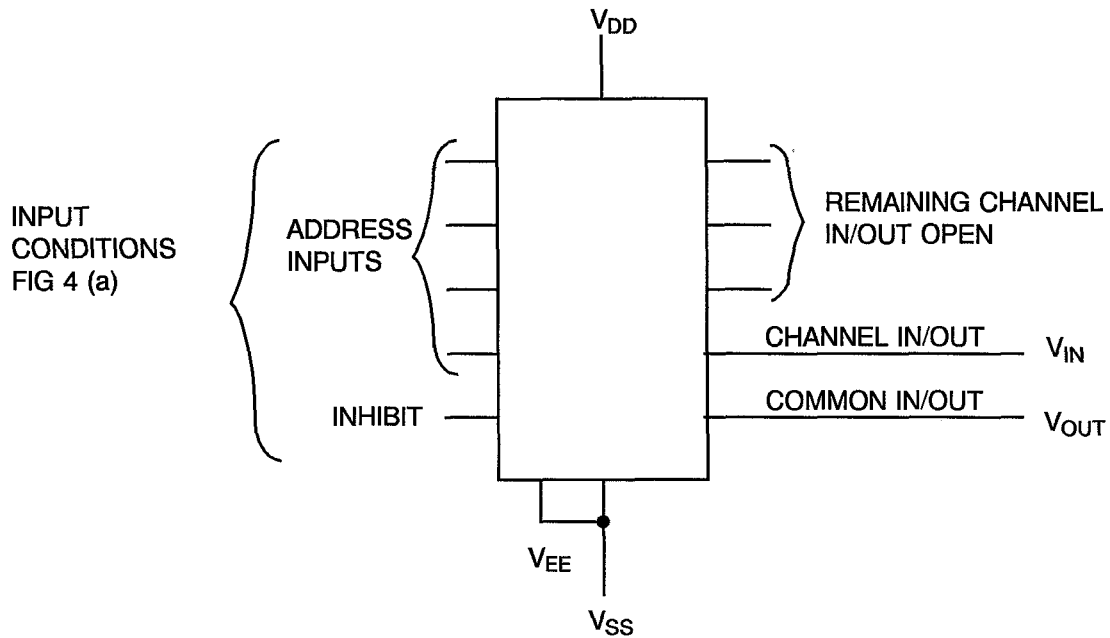
NOTES:

1. $I_I < 2\mu A$ for all OFF Channels

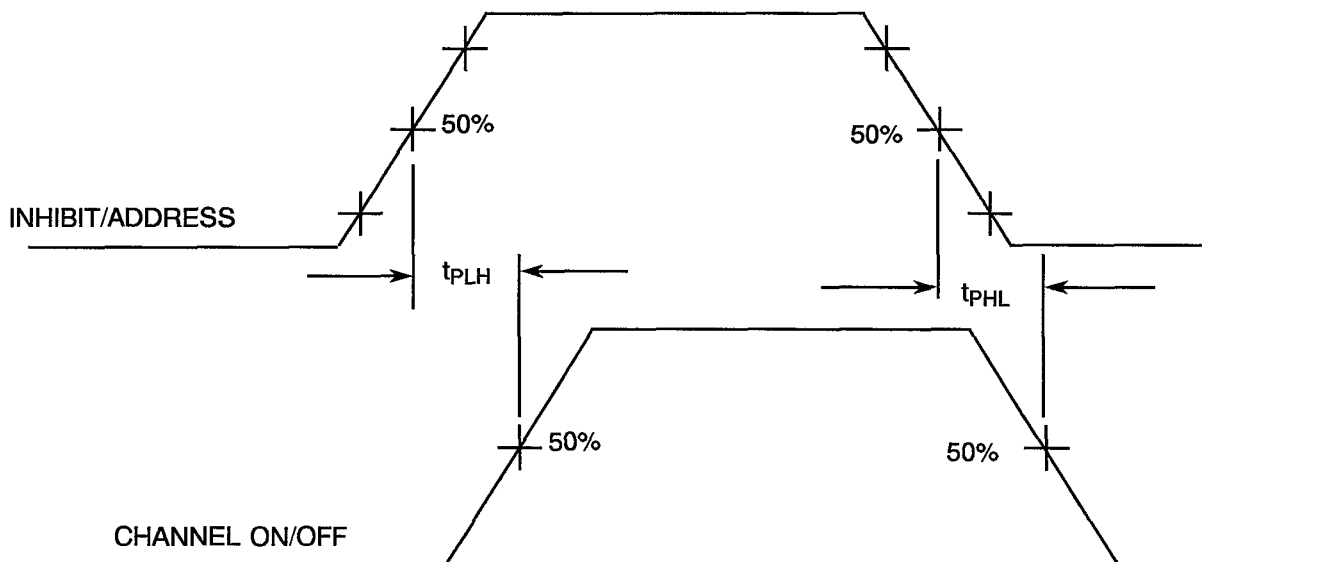


FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS (CONTINUED)

FIGURE 4(p) - PROPAGATION DELAY, INHIBIT OR ADDRESS INPUTS TO CHANNEL ON OR OFF



VOLTAGE WAVEFORMS



NOTES 1. Pulse Generator - $V_p = 0$ to V_{DD} , t_r and $t_f \leq 15ns$, $f = 500kHz$.

The terminal material and/or finish shall be in accordance with the requirements of ESCC Basic Specification No. 23500.

1.5 **MAXIMUM RATINGS**

The maximum ratings shall not be exceeded at any time during use or storage.

Maximum ratings shall only be exceeded during testing to the extent specified in this specification and when stipulated in Test Methods and Procedures of the ESCC Generic Specification.

Characteristics	Symbols	Maximum Ratings	Units	Remarks
Supply Voltage	V_{DD}	-0.5 to 18	V	Note 1
Supply Voltage Range	$V_{DD}-V_{EE}$	-0.5 to 18	V	Note 2
Control Input Voltage	V_{IN}	-0.5 to $V_{DD} +0.5$	V	Note 1 Power on
Channel Input/Output Voltage	V_{IN}	$V_{EE} -0.5$ to $V_{DD} +0.5$	V	Note 1, 3
Control Input Current	I_{IN}	± 10	mA	-
Device Power Dissipation (Continuous)	P_D	200	mW	-
Power Dissipation per Single Output	P_{DSO}	100	mW	-
Operating Temperature Range	T_{op}	-55 to +125	$^{\circ}C$	T_{amb}
Storage Temperature Range	T_{stg}	-65 to +150	$^{\circ}C$	-
Soldering Temperature For FP, DIP and SO For CCP	T_{sol}	+265 +245	$^{\circ}C$	Note 4 Note 5

NOTES:

1. Device is functional for $3V \leq V_{DD} \leq 15V$ with reference to V_{SS} .
2. Device is functional for $3V \leq V_{DD}-V_{EE} \leq 15V$.
3. To avoid draining V_{DD} supply current into the ON Channel when current flows from CH to COM the voltage drop across the ON Channel shall not exceed 0.4V.
4. Duration 10 seconds maximum at a distance of not less than 1.5mm from the device body and the same terminal shall not be resoldered until 3 minutes have elapsed.
5. Duration 5 seconds maximum and the same terminal shall not be resoldered until 3 minutes have elapsed.

1.6 **HANDLING PRECAUTIONS**

These devices are susceptible to damage by electrostatic discharge. Therefore, suitable precautions shall be employed for protection during all phases of manufacture, testing, packaging, shipment and any handling.

These components are categorised as Class 1 per ESCC Basic Specification No. 23800 with a minimum Critical Path Failure Voltage of 400 Volts.

Characteristics	Symbols	MIL-STD-883 Test Method	Test Conditions Note 1	Limits		Units
				Min	Max	
Channel OFF Leakage Current 1, Any Channel CH	I _{OFF1}	-	Channel Under Test V _{IN} (CH)=15V V _{IN} (COM)=0V All other Channels Open V _{DD} =15V, V _{SS} =V _{EE} = 0V	-	-100	nA
Channel OFF Leakage Current 2, Any Channel CH	I _{OFF2}	-	Channel Under Test V _{IN} (CH)=0V V _{IN} (COM)=15V All other Channels Open V _{DD} =15V, V _{SS} =V _{EE} = 0V	-	100	nA
Channel OFF Leakage Current 3, All Channels Tested Together	I _{OFF3}	-	V _{IN} (CH)=0V V _{IN} (COM)=15V V _{DD} =15V, V _{SS} =V _{EE} = 0V	-	100	nA
Channel OFF Leakage Current 4, All Channels Tested Together	I _{OFF4}	-	V _{IN} (CH)=15V V _{IN} (COM)=0V V _{DD} =15V, V _{SS} =V _{EE} = 0V	-	-100	nA
Channel ON Resistance 1	R _{ON1}	-	V _{IL} =0V, V _{IH} =5V R _L =10kΩ V _{DD} =5V, V _{SS} =V _{EE} = 0V Note 4	-	1050	Ω
Channel ON Resistance 2	R _{ON2}	-	V _{IL} =0V, V _{IH} =15V R _L =10kΩ V _{DD} =15V, V _{SS} =V _{EE} = 0V Note 4	-	280	Ω
Low Level Input Voltage 1 (Noise Immunity) (Functional Test)	V _{IL1}	-	Verify Truth Table V _{DD} =5V, V _{SS} =V _{EE} =0V Note 5	-	1.5	V
Low Level Input Voltage 2 (Noise Immunity) (Functional Test)	V _{IL2}	-	Verify Truth Table V _{DD} =15V, V _{SS} =V _{EE} = 0V Note 5	-	4	V
High Level Input Voltage 1 (Noise Immunity) (Functional Test)	V _{IH1}	-	Verify Truth Table V _{DD} =5V, V _{SS} =V _{EE} =0V Note 5	3.5	-	V

Characteristics	Symbols	MIL-STD-883 Test Method	Test Conditions Note 1	Limits		Units
				Min	Max	
High Level Input Voltage 2 (Noise Immunity) (Functional Test)	V_{IH2}	-	Verify Truth Table $V_{DD}=15V$, $V_{SS}=V_{EE}=0V$ Note 5	11	-	V
Threshold Voltage N-Channel	V_{THN}	-	INH Input and V_{EE} at Ground All Other Inputs: $V_{IN}=5V$ $V_{DD}=5V$, $I_{SS}=-10\mu A$	-0.7	-3	V
Threshold Voltage P-Channel	V_{THP}	-	INH Input at Ground All Other Inputs: $V_{IN}=-5V$ $V_{SS}=V_{EE}=-5V$, $I_{DD}=3.5\mu A$	0.7	3	V
Input Clamp Voltage 1, to V_{SS} , Control Inputs	V_{IC1}	-	I_{IN} (Under Test)=- -100 μA $V_{DD}=\text{Open}$, $V_{SS}=0V$ All Other Pins Open	-	-2	V
Input Clamp Voltage 2, to V_{DD} , Control Inputs	V_{IC2}	-	V_{IN} (Under Test)=6V $R=30k\Omega$, $V_{SS}=\text{Open}$ All Other Pins Open Note 6	3	-	V
Input Capacitance, Control Inputs	C_{IN}	3012	V_{IN} (Not Under Test)=0V $V_{DD}=V_{SS}=V_{EE}=0V$ $f=100\text{ kHz to }1\text{ MHz}$ Note 7	-	7.5	pF
Channel Capacitance, CH	C_{CH}	3012	V_{IN} (Not Under Test)=0V $V_{DD}=V_{SS}=V_{EE}=0V$ $f=100\text{ kHz to }1\text{ MHz}$ Note 7	-	7.5	pF
Channel Capacitance, XCOM, YCOM	C_{COM}	3012	V_{IN} (Not Under Test)=0V $V_{DD}=V_{SS}=V_{EE}=0V$ $f=100\text{ kHz to }1\text{ MHz}$ Note 7	-	30	pF
Propagation Delay Low to High 1, XCOM to XCH0	t_{PLH1}	3003	$V_{IN}(\text{COM})=\text{Pulse Generator}$ V_{IN} (Remaining Inputs)=Truth Table $V_{IL}=0V$, $V_{IH}=5V$, $R_L=200k\Omega$ $V_{DD}=5V$, $V_{SS}=V_{EE}=0V$ Note 8	-	40	ns

Characteristics	Symbols	MIL-STD-883 Test Method	Test Conditions Note 1	Limits		Units
				Min	Max	
Propagation Delay High to Low 1, XCOM to CH0	t _{PHL1}	3003	V _{IN} (COM)=Pulse Generator V _{IN} (Remaining Inputs)=Truth Table V _{IL} =0V, V _{IH} =5V, R _L =200kΩ V _{DD} =5V, V _{SS} =V _{EE} =0V Note 8	-	40	ns
Propagation Delay Low to High 2, A to YCOM (Channels ON)	t _{PLH2}	3003	V _{IN} (A)=Pulse Generator V _{IN} (Remaining Inputs)=Truth Table V _{IL} =0V, V _{IH} =5V, V _{IN} (CH)=0V and 5V R _L =10kΩ V _{DD} =5V, V _{SS} =V _{EE} =0V Note 8	-	720	ns
Propagation Delay High to Low 2, A to YCOM (Channels ON)	t _{PHL2}	3003	V _{IN} (A)=Pulse Generator V _{IN} (Remaining Inputs)=Truth Table V _{IL} =0V, V _{IH} =5V, V _{IN} (CH)=0V and 5V R _L =10kΩ V _{DD} =5V, V _{SS} =V _{EE} =0V Note 8	-	720	ns
Output Enable Time High Impedance to High Output, INH to YCOM	t _{PZH}	3003	V _{IN} (INH)=Pulse Generator V _{IN} (Remaining Inputs)=Truth Table V _{IL} =0V, V _{IH} =5V, V _{IN} (CH)=5V, R _L =10kΩ V _{DD} =5V, V _{SS} =V _{EE} =0V Note 8	-	400	ns
Output Disable Time High Output to High Impedance, INH to YCOM	t _{PHZ}	3003	V _{IN} (INH)=Pulse Generator V _{IN} (Remaining Inputs)=Truth Table V _{IL} =0V, V _{IH} =5V, V _{IN} (CH)=5V, R _L =300Ω V _{DD} =5V, V _{SS} =V _{EE} =0V Note 8	-	400	ns

2.3.2 High and Low Temperatures Electrical Measurements

The measurements shall be performed at T_{amb}=+125 (+0 -5) °C and T_{amb}=- 55(+5-0)°C.

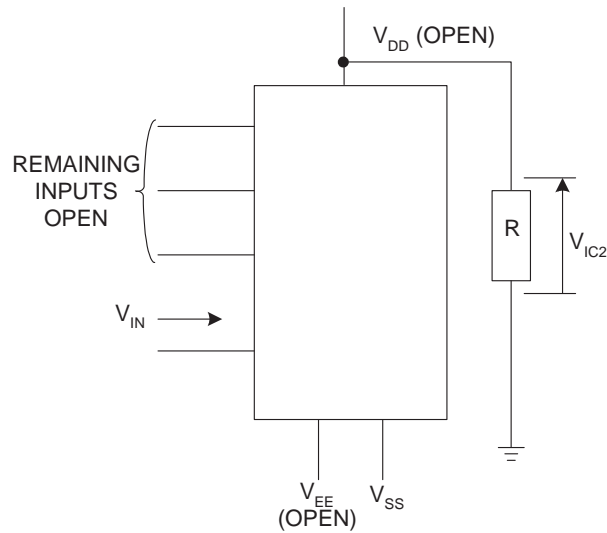
Characteristics	Symbols	MIL-STD-883 Test Method	Test Conditions Note 1	Limits		Units
				Min	Max	
Threshold Voltage P-Channel	V_{THP}	-	INH Input at Ground All Other Inputs: $V_{IN}=-5V$ $V_{SS}=V_{EE}=-5V,$ $I_{DD}=3.5\mu A$ $T_{amb}=+125^{\circ}C$ $T_{amb}=-55^{\circ}C$	0.3 0.7	3.5 3.5	V

2.3.3 Notes to Electrical Measurement Tables

1. Unless otherwise specified all inputs and channels shall be tested for each characteristic, inputs not under test shall be $V_{IN} = V_{SS}$ or V_{DD} and channels not under test shall be open.
2. Functional tests shall be performed to verify Truth Table. The Maximum time to output comparator strobe = 300 μ s.
3. Quiescent Current shall be tested using the following input conditions where 1 = V_{IH} and 0 = V_{IL} :

TEST	INPUT CONDITIONS												
	INH	A	B	XCOM	XCH0	XCH1	XCH2	XCH3	YCOM	YCH0	YCH1	YCH2	YCH3
(a)	0	0	0	1	1	1	1	1	1	1	1	1	1
(b)	0	1	0	1	1	1	1	1	1	1	1	1	1
(c)	0	0	1	0	0	0	0	0	0	0	0	0	0
(d)	0	1	1	0	0	0	0	0	0	0	0	0	0
(e)	1	0	0	1	1	1	1	1	1	1	1	1	1

4. Channel ON Resistance shall be tested for each channel in both directions using the following input conditions:
 - (a) $INH = V_{IL}$
 - (b) A, B = V_{IL} or V_{IH} per Truth Table to select channel under test.
 - (c) I_{IN} (CH or COM) = 100 μ A.
 - (d) R_{ON1} shall be tested with V_{IN} (CH or COM)= 1.5V, 1.9V, 2.3V, 2.7V, 3.3V, 3.7V, 4.1V.
 R_{ON2} shall be tested with V_{IN} (CH or COM)= 1.5V, 1.9V, 2.3V, 2.7V, 13.3V, 13.7V, 14.1V, 14.5V.
 Channel ON Resistance shall be recorded for Channel Y0 (YCH0 to YCOM, YCOM to YCH0) at each specified V_{IN} . Other channels may be tested go-no-go.
5. Performed as a functional test to verify for all OFF channels $I_{OFF}<2\mu A$ with V_{IN} (CH)= V_{DD} through 1k Ω , COM output load resistance $R_L=1k\Omega$.
6. Input Clamp Voltage 2 to V_{DD} , V_{IC2} , shall be tested on each input as follows:-

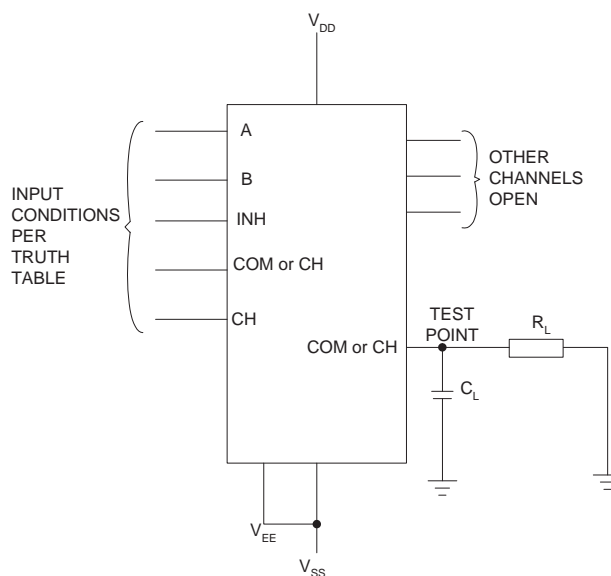


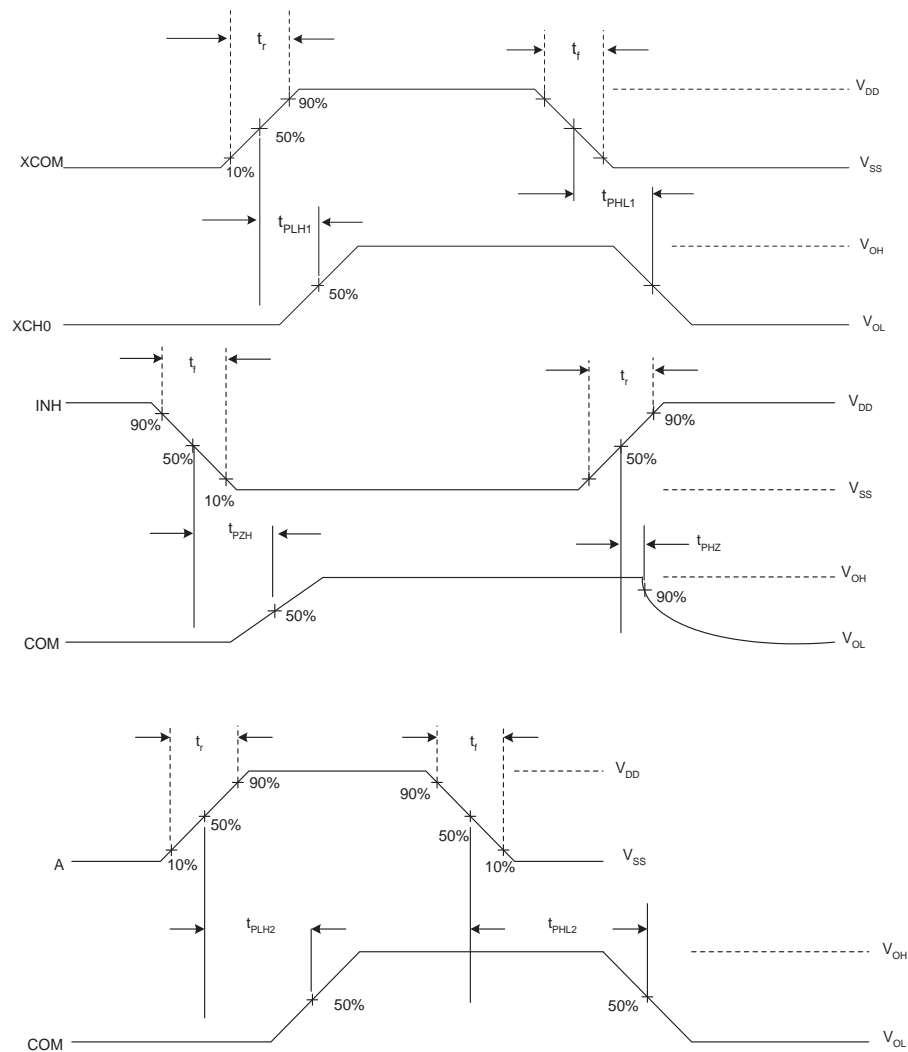
7. Guaranteed but not tested.
8. Read and record measurements shall be performed on a sample of 32 components with 0 failures permitted.

The pulse generator shall have the following characteristics:

$V_{GEN} = 0$ to V_{DD} ; $f = 500\text{kHz}$; t_r and $t_f \leq 15$ ns (10% to 90%); duty cycle = 50%. Output load capacitance $C_L = 50\text{pF} \pm 5\%$ including scope probe, wiring and stray capacitance without component in the test fixture. Channel bias resistance $R_L =$ as specified.

Propagation delay times shall be measured as follows:





2.4

PARAMETER DRIFT VALUES

Unless otherwise specified, the measurements shall be performed at $T_{amb}=+22 \pm 3^{\circ}C$.

The test methods and test conditions shall be as per the corresponding test defined in Room Temperature Electrical Measurements.

The drift values (Δ) shall not be exceeded for each characteristic specified. The corresponding absolute limit values for each characteristic shall not be exceeded.